

N-channel 100 V, 156 mΩ logic level MOSFET in LFPAK33 19 September 2016 Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	9.3	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	36	W
Static charact	eristics	·					
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>		-	124	156	mΩ
Dynamic characteristics							
Q _{GD}	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 13}}{13}; \frac{\text{Fig. 14}}{14}$		-	3.2	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D
2	S	Source		
3	S	Source	\bigcirc	G-UTA
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUK9M156-100E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9M156-100E	915610

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	100	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; T _j ≤ 175 °C	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	36	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	9.3	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	6.5	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3		-	37	А

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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
I _S	source current	T _{mb} = 25 °C		-	9.3	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	37	А
Avalanche r	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} {\sf I}_{\sf D} = 9.3 \; {\sf A}; \; {\sf V}_{\sf sup} \le 100 \; {\sf V}; \; {\sf R}_{\sf GS} = 50 \; \Omega; \\ {\sf V}_{\sf GS} = 5 \; {\sf V}; \; {\sf T}_{\sf j(init)} = 25 \; {}^\circ{\sf C}; \; {\sf unclamped}; \\ \hline {\sf Fig. 4} \end{array}$	[3][4]	-	9.6	mJ

[1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.

[2] Significantly longer life times are achieved by lowering T_i and or V_{GS}

[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[4] Refer to application note AN10273 for further information.

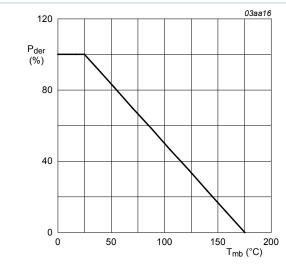
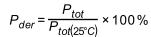


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



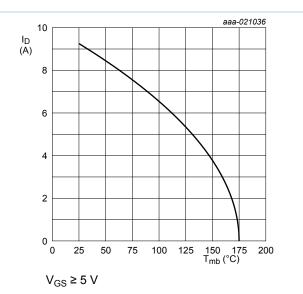
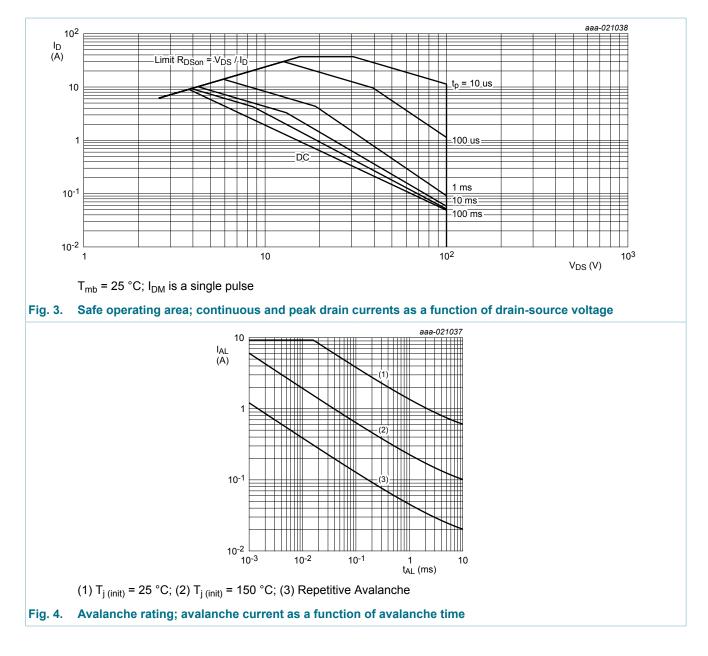


Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 9.3A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

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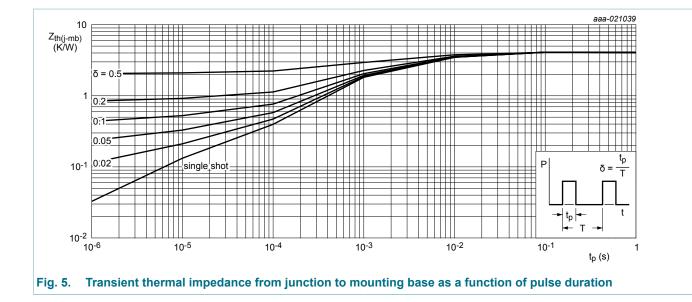


9. Thermal characteristics

Table 6. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	3.61	4.17	K/W

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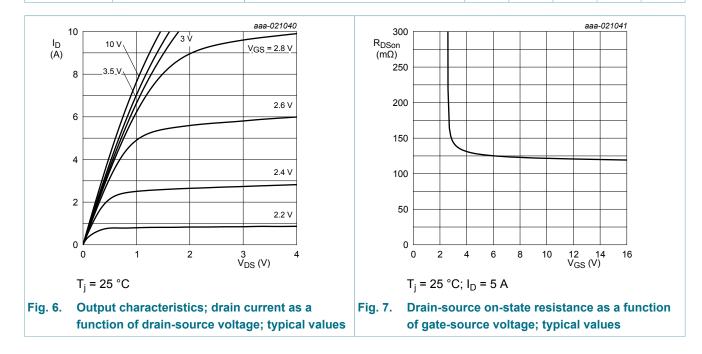
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · ·				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
breakdown voltage	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.45	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V
I _{DSS} drain leakage curre	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.01	1	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	124	156	mΩ
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	120	150	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; <u>Fig. 12</u>	-	-	420	mΩ
Dynamic cł	naracteristics	· ·	1			
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 80 V; V _{GS} = 5 V;	-	7.4	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	1.4	-	nC
Q _{GD}	gate-drain charge		-	3.2	-	nC

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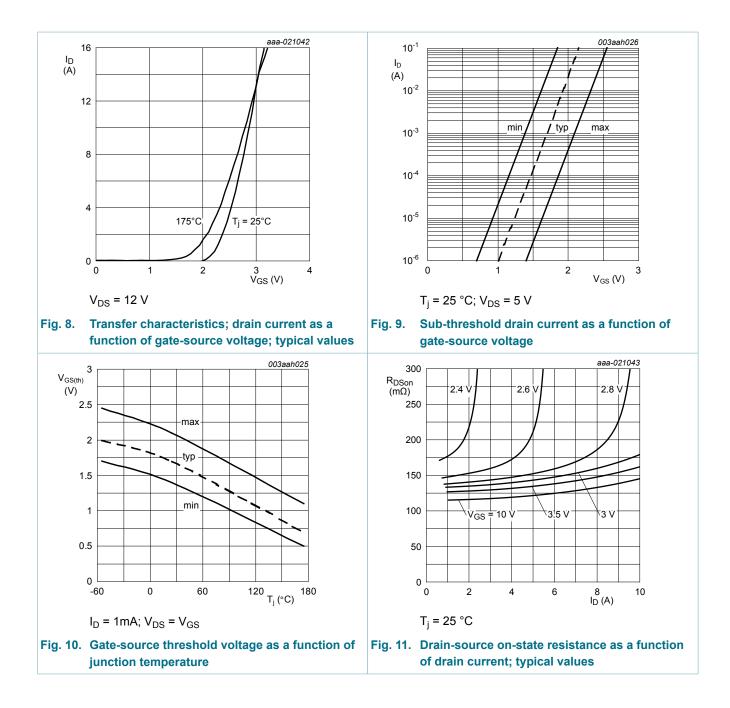
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;		-	523	695	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	42	50	pF
C _{rss}	reverse transfer capacitance			-	28	39	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R _L = 10 Ω; V _{GS} = 5 V; R _{G(ext)} = 5 Ω; T _j = 25 °C		-	5.6	-	ns
t _r	rise time			-	8.8	-	ns
t _{d(off)}	turn-off delay time			-	11.8	-	ns
t _f	fall time	-		-	7.2	-	ns
Source-dra	in diode		1	1			
V _{SD}	source-drain voltage	I_{S} = 10 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>		-	0.92	1.2	V
t _{rr}	reverse recovery time	I_{S} = 5 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V; V _{DS} = 25 V; T _j = 25 °C		-	27.6	-	ns
Q _r	recovered charge			-	33.9	-	nC



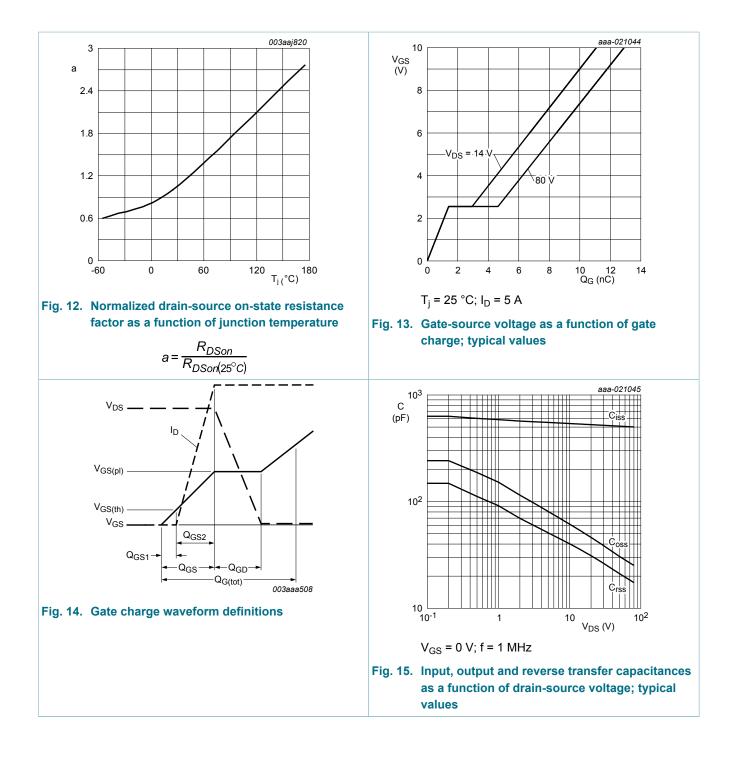
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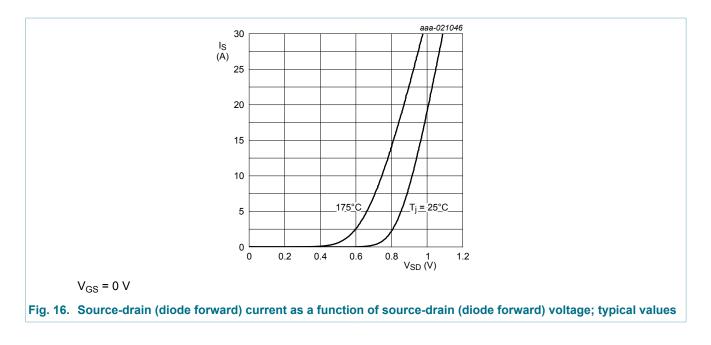
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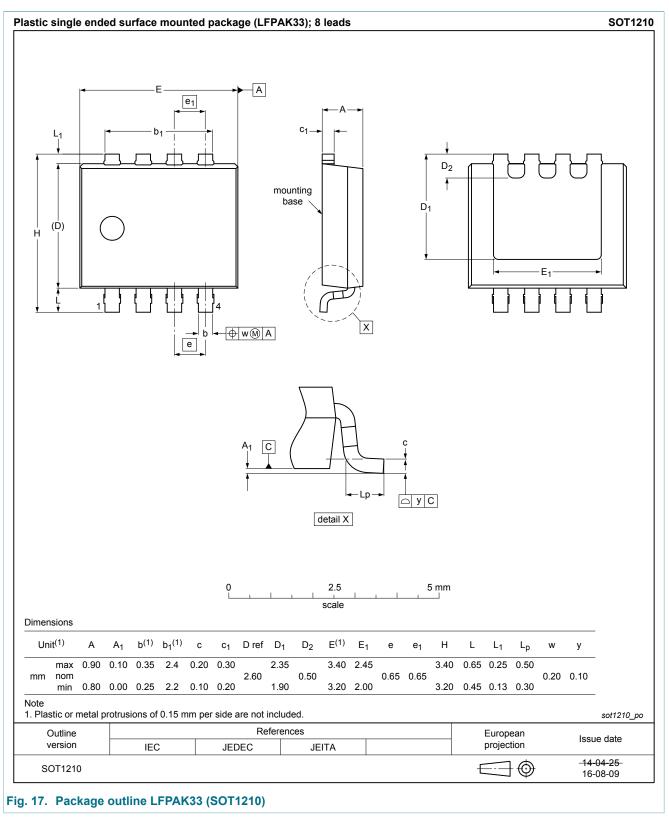


11. Application information

For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

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12. Package outline



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Product data sheet

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13. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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